## **CLAIMS**

## What is claimed is:

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- A sublamination material, comprising:
- a single layer reference plane having a top surface and a bottom surface;
  a first signal layer coupled to the top surface with a core material;
  a second signal layer coupled to the bottom surface with a bond-ply material; and
- at least one of a blind via or a micro via.
- 2. The sublamination material of claim 1, wherein the reference plane comprises a conductive material.
- 3. The sublamination material of claim 2, wherein the conductive material is copper.
- 4. The sublamination material of claim 1, wherein the first signal layer comprises the same material as the second signal layer.
- 5. The sublamination material of claim 1, wherein the first signal layer is copper.
- 6. The sublamination material of claim 1, wherein the bond-ply material comprises the same material as the core material.
- 7. The sublamination material of claim 1, wherein the core material is a dielectric material.
- 8. The sublamination material of claim 7, wherein the dielectric material is FR4.
- 9. The sublamination material of claim 1, wherein the second signal layer comprises copper.
- 10. The sublamination material of claim 1, wherein the bond-ply material is a dielectric material.
- 11. The sublamination material of claim 10, wherein the dielectric material is BT.
- 25 12. The sublamination material of claim 1, wherein the blind via is formed by using a laser or a conventional drill.
  - 13. A method of producing a sublamination material, comprising:

    providing a core material, wherein the core material is sandwiched on both sides by a
    layer of conductive material;
- applying a photoresist to the layers of conductive material;

imaging one layer of the conductive material to produce an imaged layer of conductive material;

developing and etching the imaged layer of the conductive material to produce an etched layer of conductive material;

- stripping the photoresist from both layers of conductive material; applying a bonding material to the etched layer of conductive material; coupling a second metal layer to the bonding material to form a layered stack; curing the layered stack; and drilling at least one blind via or nicro via into the sublamination material.
- 10 14. The method of claim 13, wherein the layer of conductive material is copper.
  - 15. The method of claim 13, where in the bonding material is FR4.
  - 16. A method for producing an electronic component, comprising:
    providing a substrate;
    coupling at least one sublamination material to the substrate; and
    coupling at least one additional layer to the sublamination material.
  - 17. The method of claim 16, wherein the substrate is a silicon wafer.
  - 18. The method of claim 16, wherein the sublamination material is the sublamination material of claim 1.
  - 19. The method of claim 16, wherein the additional layer is a laminate.
- 20 20. The method of claim 16, wherein the electronic component comprises a printed circuit board.

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